Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5498	(teos near based)(tetraethyl near orthosilicate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 16:17
L2	745	1 with oxide with (procedure process method)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 16:19
L3	52	2 with depositing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 16:07
L4	4	("5726090" | "5804259" | "5814564" | "5817567").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/11 16:13
L5	5498	(teos near1 based)(tetraethyl near1 orthosilicate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 16:17
L6	703	1 with oxide with deposit$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 16:18
L7	228	6 with (procedure process method)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 16:41
L8	9	7 with metal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 16:41

L9	3	8 with etch$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 16:19
L10	5	7 same (metal near layer) same etch$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 16:41
L11	30	6 same (metal near layer) same etch$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 16:41
L12	30	11 and (procedure process method)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 16:42